SNV/U High Performances UV Microchip Series

Key features

- **355nm and 266nm**
- Repetition rate up to 20kHz
- Ultrashort pulses down to 550ps
- Multi-kW peak power
- Excellent beam quality
- Efficient, air-cooled
- Sealed package, extremely long life



For generating high peak power ultraviolet pulses of a few hundred picoseconds, microchip lasers are economical, compact, and reliable. Microjoule UV pulses are generated from the harmonic conversion of the emissions from a passively Q-switched Nd:YAG microchip engine. The SNV and SNU series are designed for high average power, delivering multi-kW peak power at repetition rates up to 20kHz.

Applications

- Semiconductor inspection
- Laser-induced fluorescence (LIF)
- Micro dissection
- Organic compound marking and micromachining
- Biohazard detection
- Time resolved fluorescence
- Laser Induced Breakdown Spectroscopy (LIBS)

Technical specifications:

	SNV-05P-100	SNV-20F-100 ⁽⁸⁾	SNU-02P-100	SNU-20F-100
Wavelength	355nm	355nm	266nm	266nm
Repetition Rate	>5kHz	>19kHz	>6kHz	>19kHz
Constant Pulse width range (FWHM) (1)		<0.6ns <0.6ns		<0.6ns
Output power ⁽²⁾	>5mW	>10mW	>2mW	>10mW
Output energy	>0.5µJ	>0.5µJ	>0.3µJ	>0.5µJ
Peak Power	>0.7kW	0.7kW	>0.5kW	>0.7kW
Short term (1min) power stability (3)	<±1%	<±1%	<±1%	<±2%
Long term (6 hrs) power stability ⁽³⁾	<±5%	<±5% <±5%		<±5%
Beam profile	Gaussian TEM00	Gaussian TEM00	See note (6)	See note (6)
Full angle divergence Horizontal@1/e² Vertical@1/e²	8.5±2mrad 6±2mrad	11±2mrad 7±2mrad	11±2mrad <1.5mm ⁽⁷⁾	11.5±2mrad 0.65±0.25mrad
M ²⁽⁴⁾	<1.3	<1.3	<1.3	<1.4
Beam ellipticity ⁽⁵⁾	<1.3	<1.3 N/A		N/A
Gaussian fit in far field	N/A	N/A N/A		>85%
Polarization	Linear PER>20dB	Linear PER>20dB	Linear PER>20dB	Linear PER>20dB
Package dimensions	180x55x36mm	186x60x36mm	180x55x36mm	210x60x36mm
Package weight	400g	500g	400g	500g
Options (table p3)	С	С	С	С
Options included	-	S	-	S

	Notes
_ (1) _	Measured with 1Ghz photodiode and 1GHz/10GS/s oscilloscope.
(2)	Measurement performed with an OPHIR thermal power sensor (OPHIR 3A-FS-SH)
(3)	For temperature variation $< \pm 3$ °C and < 3 °C/hour, stability is measured with calorimeter - detector band [DC, 2Hz]
(4)	Mean average value $M = \sqrt{(XY)}$, X and Y being respectively the major and minor axis of the ellipse
(5)	Beam ellipticity is calculated as the ratio of the main axis far field divergence
(6)	Beam exhibits different profile in horizontal (Gaussian) and vertical (($\sin x/x$) ² in far-field) plan
(7)	5%/95% diameter, at 300mm from laser output
(8)	Contact factory for availability

Complementary information & options:

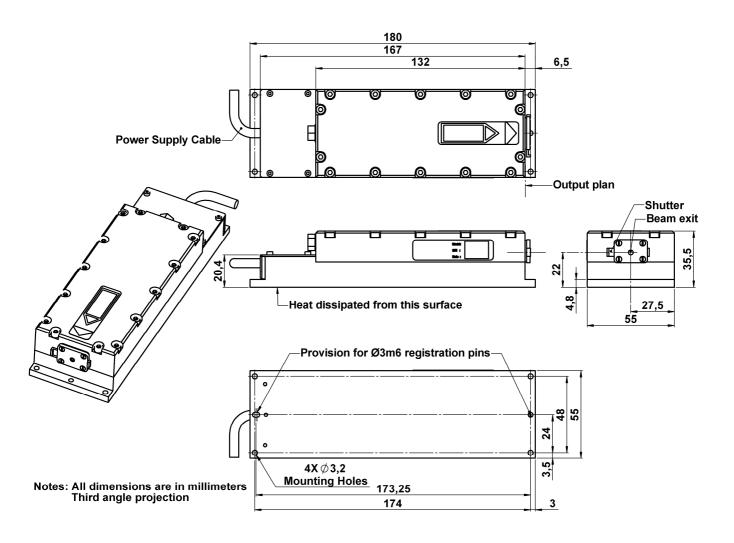
Environment Parameters			
Operating Temperature Range	15-35°C		
Maximum Laser Head Baseplate Temperature	<50°C		
Maximum Power Consumption	<40W		
Laser Head Thermal Dissipation	<15W		
Storage Temperature	0-50°C		
Shock of 11ms according to IEC 68- 2-27, non operating	25g		
Vibration 5Hz to 500Hz sinusoïdal according to IEC 68-2-6	2 g		

Certification				
Laser classification according to IEC 60825-1:2007	3B for SNV-05P and SNV-20F 4 for SNU-02P and SNU-20F			
CDRH	Yes, if used with a -DR1 controller			
ROHs	Yes			

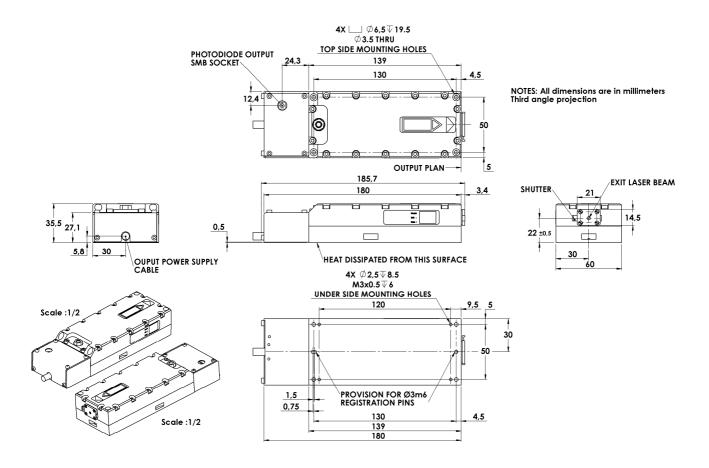
Options			
Collimation (C)	With collimated beam		
Synchronization output (S)	TTL compatible output signal for synchronization/monitoring		

Available Controller Types					
Model	Туре	Input Power	CDRH		
MLC-03A-DR1	Desktop	100-240 V AC	Yes		
MLC-03A-MR1	Module	12 V DC	No		
MLC-03A-BR1	Board	12 V DC	No		

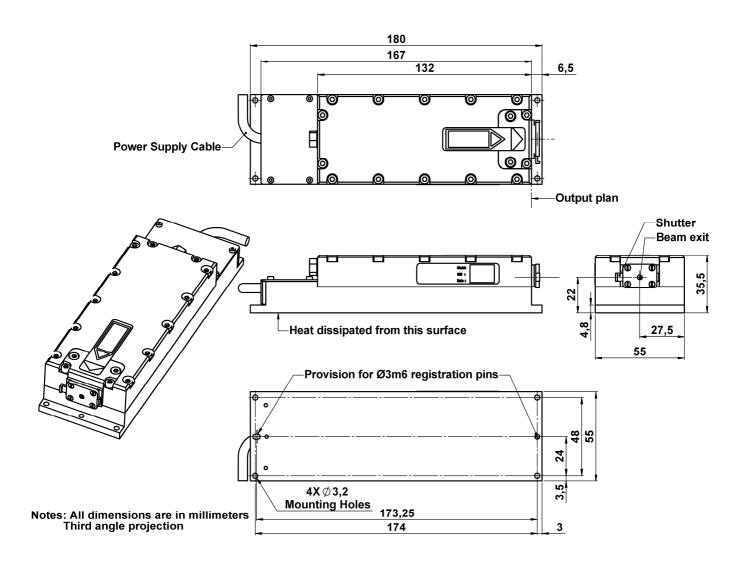
CDRH Laser Head Mechanical Drawings: SNV-05P-100



CDRH Laser Head Mechanical Drawings: SNV-20F-100



CDRH Laser Head Mechanical Drawings: SNU-02P-100



CDRH Laser Head Mechanical Drawings: SNU-20F-100

